

TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74VCX16721FT

Low-Voltage 20-Bit D-Type Flip-Flop with 3.6-V Tolerant Inputs and Outputs

The TC74VCX16721FT is a high-performance CMOS 20-bit D-type flip-flop. Designed for use in 1.8-V, 2.5-V or 3.3-V systems, it achieves high-speed operation while maintaining the CMOS low power dissipation.

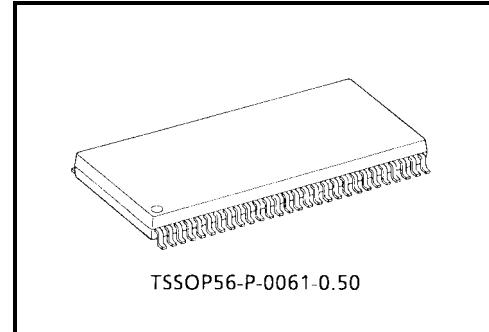
It is also designed with overvoltage tolerant inputs and outputs up to 3.6 V.

The TC74VCX16721FT is edge-triggered D-type flip-flop with qualified clock storage. On the positive transition of the clock (CK) input, the device provides true data at the Q outputs if the clock-enable (\overline{CKEN}) input is low. If \overline{CKEN} is high, no data is stored. When the OE input is high, the outputs are in a high-impedance state. This device is designed to be used with 3-state memory address drivers, etc.

All inputs are equipped with protection circuits against static discharge.

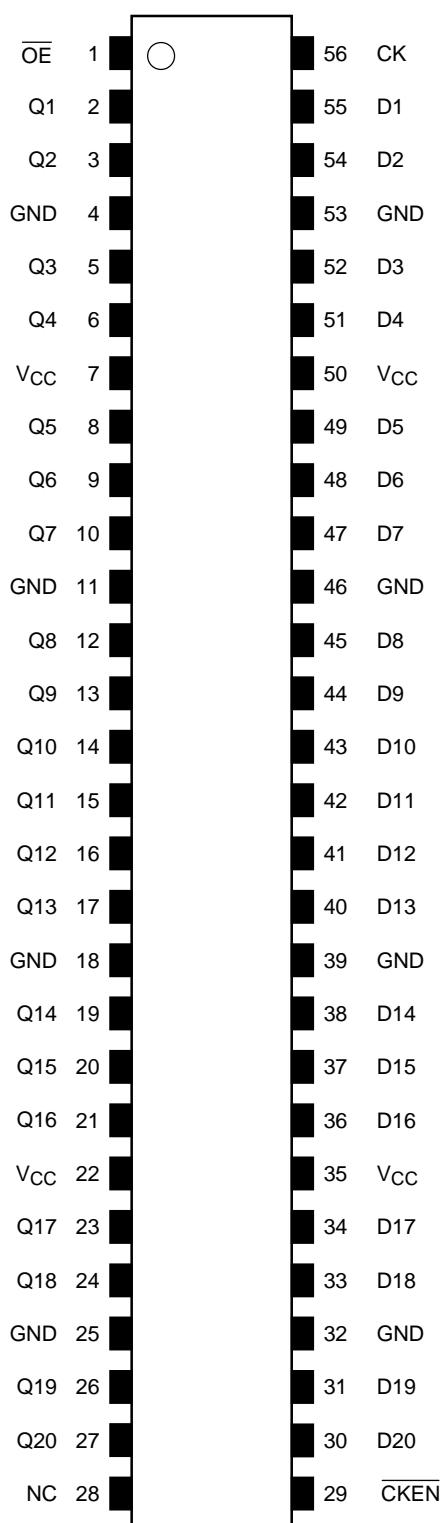
Features

- Low-voltage operation: $V_{CC} = 1.8$ to 3.6 V
- High-speed operation: $t_{pd} = 3.5$ ns (max) ($V_{CC} = 3.0$ to 3.6 V)
 - : $t_{pd} = 4.4$ ns (max) ($V_{CC} = 2.3$ to 2.7 V)
 - : $t_{pd} = 8.8$ ns (max) ($V_{CC} = 1.8$ V)
- Output current: $I_{OH}/I_{OL} = \pm 24$ mA (min) ($V_{CC} = 3.0$ V)
 - : $I_{OH}/I_{OL} = \pm 18$ mA (min) ($V_{CC} = 2.3$ V)
 - : $I_{OH}/I_{OL} = \pm 6$ mA (min) ($V_{CC} = 1.8$ V)
- Latch-up performance: ± 300 mA
- ESD performance: Machine model $> \pm 200$ V
 - : Human body model $> \pm 2000$ V
- Package: TSSOP (thin shrink small outline package)
- 3.6-V tolerant function and power-down protection provided on all inputs and outputs

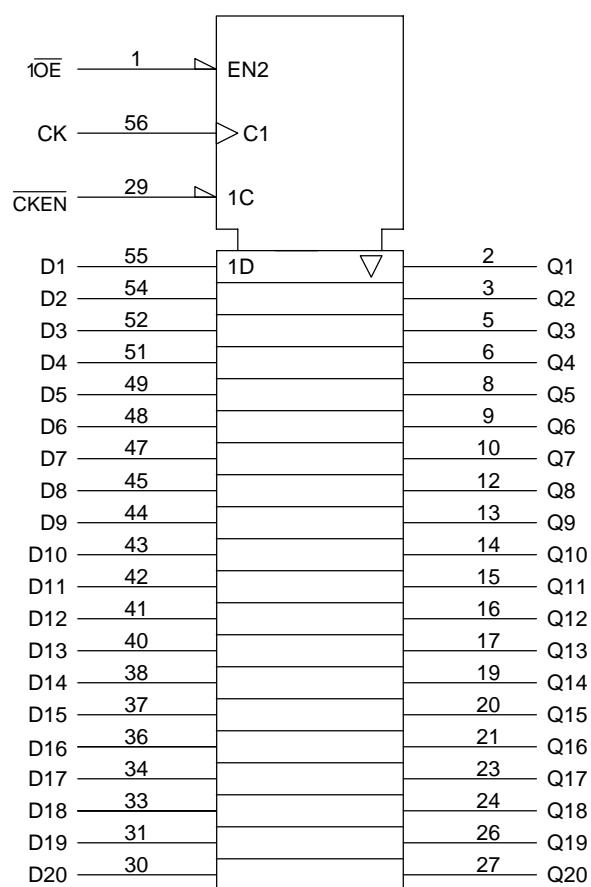


Weight: 0.25 g (typ.)

Pin Assignment (top view)



IEC Logic Symbol



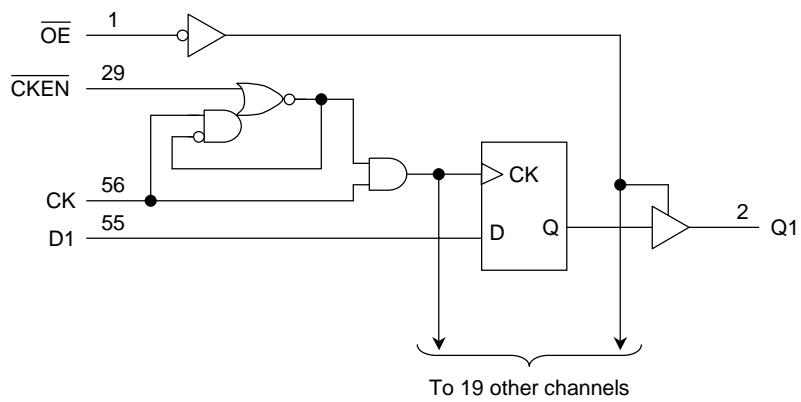
Truth Table (each flip-flop)

Inputs				Outputs Q
\overline{OE}	\overline{CKEN}	CK	D	
L	H	X	X	Q0
L	L	↑	H	H
L	L	↑	L	L
L	L	L or H	X	Q0
H	X	X	X	Z

X: Don't care

Z: High impedance

Qn: No change

System Diagram

Maximum Ratings

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	–0.5 to 4.6	V
DC input voltage	V _{IN}	–0.5 to 4.6	V
DC output voltage	V _{OUT}	–0.5 to 4.6 (Note 1)	V
		–0.5 to V _{CC} + 0.5 (Note 2)	
Input diode current	I _{IK}	–50	mA
Output diode current	I _{OK}	±50 (Note 3)	mA
DC output current	I _{OUT}	±50	mA
Power dissipation	P _D	400	mW
DC V _{CC} /ground current per supply pin	I _{CC} /I _{GND}	±100	mA
Storage temperature	T _{stg}	–65 to 150	°C

Note 1: OFF state

Note 2: High or low state. I_{OUT} absolute maximum rating must be observed.

Note 3: V_{OUT} < GND, V_{OUT} > V_{CC}

Recommended Operating Range

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	1.8 to 3.6	V
		1.2 to 3.6 (Note 4)	
Input voltage	V _{IN}	–0.3 to 3.6	V
Output voltage	V _{OUT}	0 to 3.6 (Note 5)	V
		0 to V _{CC} (Note 6)	
Output current	I _{OH} /I _{OL}	±24 (Note 7)	mA
		±18 (Note 8)	
		±6 (Note 9)	
Operating temperature	T _{opr}	–40 to 85	°C
Input rise and fall time	dt/dv	0 to 10 (Note 10)	ns/V

Note 4: Data retention only

Note 5: OFF state

Note 6: High or low state

Note 7: V_{CC} = 3.0 to 3.6 V

Note 8: V_{CC} = 2.3 to 2.7 V

Note 9: V_{CC} = 1.8 V

Note 10: V_{IN} = 0.8 to 2.0 V, V_{CC} = 3.0 V

Electrical Characteristics**DC Characteristics (Ta = -40 to 85°C, 2.7 V < V_{CC} ≤ 3.6 V)**

Characteristics		Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit	
Input voltage	H-level		—	2.7 to 3.6					
	L-level	V _{IL}	—	2.7 to 3.6	—	0.8	—		
Output voltage	H-level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	2.7 to 3.6	V _{CC} - 0.2	—	V	
				I _{OH} = -12 mA	2.7	2.2	—		
				I _{OH} = -18 mA	3.0	2.4	—		
				I _{OH} = -24 mA	3.0	2.2	—		
	L-level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	2.7 to 3.6	—	0.2		
				I _{OL} = 12 mA	2.7	—	0.4		
				I _{OL} = 18 mA	3.0	—	0.4		
				I _{OL} = 24 mA	3.0	—	0.55		
Input leakage current		I _{IN}	V _{IN} = 0 to 3.6 V		2.7 to 3.6	—	±5.0	μA	
3-state output OFF state current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0 to 3.6 V		2.7 to 3.6	—	±10.0	μA	
Power-off leakage current		I _{OFF}	V _{IN} , V _{OUT} = 0 to 3.6 V		0	—	10.0	μA	
Quiescent supply current		I _{CC}	V _{IN} = V _{CC} or GND V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		2.7 to 3.6	—	20.0	μA	
Increase in I _{CC} per input		ΔI _{CC}	V _{IH} = V _{CC} - 0.6 V		2.7 to 3.6	—	750		

DC Characteristics (Ta = -40 to 85°C, 2.3 V ≤ V_{CC} ≤ 2.7 V)

Characteristics		Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit	
Input voltage	H-level		—	2.3 to 2.7	1.6	—			
	L-level	V _{IL}	—	2.3 to 2.7	—	0.7			
Output voltage	H-level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	2.3 to 2.7	V _{CC} - 0.2	—	V	
				I _{OH} = -6 mA	2.3	2.0	—		
				I _{OH} = -12 mA	2.3	1.8	—		
				I _{OH} = -18 mA	2.3	1.7	—		
	L-level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	2.3 to 2.7	—	0.2		
				I _{OL} = 12 mA	2.3	—	0.4		
				I _{OL} = 18 mA	2.3	—	0.6		
				I _{OL} = 24 mA	2.3 to 2.7	—	0.55		
Input leakage current		I _{IN}	V _{IN} = 0 to 3.6 V		2.3 to 2.7	—	±5.0	μA	
3-state output OFF state current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0 to 3.6 V		2.3 to 2.7	—	±10.0	μA	
Power-off leakage current		I _{OFF}	V _{IN} , V _{OUT} = 0 to 3.6 V		0	—	10.0	μA	
Quiescent supply current		I _{CC}	V _{IN} = V _{CC} or GND V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		2.3 to 2.7	—	20.0	μA	

DC Characteristics ($T_a = -40$ to 85°C , $1.8 \text{ V} \leq V_{CC} < 2.3 \text{ V}$)

Characteristics		Symbol	Test Condition		$V_{CC} (\text{V})$	Min	Max	Unit	
Input voltage	H-level	V_{IH}	—		1.8 to 2.3	$0.7 \times V_{CC}$	—	V	
	L-level	V_{IL}	—		1.8 to 2.3	—	$0.2 \times V_{CC}$		
Output voltage	H-level	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -100 \mu\text{A}$	1.8	$V_{CC} - 0.2$	—	V	
				$I_{OH} = -6 \text{ mA}$	1.8	1.4	—		
	L-level	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100 \mu\text{A}$	1.8	—	0.2		
				$I_{OL} = 6 \text{ mA}$	1.8	—	0.3		
Input leakage current		I_{IN}	$V_{IN} = 0$ to 3.6 V		1.8	—	± 5.0	μA	
3-state output OFF state current		I_{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = 0$ to 3.6 V		1.8	—	± 10.0	μA	
Power-off leakage current		I_{OFF}	$V_{IN}, V_{OUT} = 0$ to 3.6 V		0	—	10.0	μA	
Quiescent supply current		I_{CC}	$V_{IN} = V_{CC}$ or GND		1.8	—	20.0	μA	
			$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3.6 \text{ V}$		1.8	—	± 20.0		

AC Characteristics (Ta = -40 to 85°C, input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF, $R_L = 500$ Ω)

Characteristics	Symbol	Test Condition	V_{CC} (V)	Min	Max	Unit
			1.8			
Maximum clock frequency	f_{max}	Figure 1, Figure 2	2.5 ± 0.2	200	—	MHz
			3.3 ± 0.3	250	—	
			1.8	1.5	8.8	
Propagation delay time (CK-Q)	t_{pLH} t_{pHL}	Figure 1, Figure 2	2.5 ± 0.2	1.0	4.4	ns
			3.3 ± 0.3	0.8	3.5	
			1.8	1.5	9.8	
3-state output enable time	t_{pZL} t_{pZH}	Figure 1, Figure 3	2.5 ± 0.2	1.0	4.9	ns
			3.3 ± 0.3	0.8	3.8	
			1.8	1.5	7.6	
3-state output disable time	t_{pLZ} t_{pHZ}	Figure 1, Figure 3	2.5 ± 0.2	1.0	4.2	ns
			3.3 ± 0.3	0.8	3.7	
			1.8	4.0	—	
Minimum pulse width (CK)	t_W (H) t_W (L)	Figure 1, Figure 2	2.5 ± 0.2	1.5	—	ns
			3.3 ± 0.3	1.5	—	
			1.8	2.5	—	
Minimum setup time (D, \overline{CKEN})	t_s	Figure 1, Figure 2, Figure 4	2.5 ± 0.2	1.5	—	ns
			3.3 ± 0.3	1.5	—	
			1.8	1.0	—	
Minimum hold time (D, \overline{CKEN})	t_h	Figure 1, Figure 2, Figure 4	2.5 ± 0.2	1.0	—	ns
			3.3 ± 0.3	1.0	—	
			1.8	—	0.5	
Output to output skew	t_{osLH} t_{osHL}	(Note 11)	2.5 ± 0.2	—	0.5	ns
			3.3 ± 0.3	—	0.5	

For $C_L = 50$ pF, add approximately 300 ps to the AC maximum specification.

Note 11: Parameter guaranteed by design.

$$(t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLm} - t_{pHLn}|)$$

Dynamic Switching Characteristics(Ta = 25°C, input: t_r = t_f = 2.0 ns, C_L = 30 pF, R_L = 500 Ω)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Typ.	Unit
Quiet output maximum dynamic V _{OL}	V _{OLP}	V _{IH} = 1.8 V, V _{IL} = 0 V (Note 12)	1.8	0.25	V
		V _{IH} = 2.5 V, V _{IL} = 0 V (Note 12)	2.5	0.6	
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note 12)	3.3	0.8	
Quiet output minimum dynamic V _{OL}	V _{OLV}	V _{IH} = 1.8 V, V _{IL} = 0 V (Note 12)	1.8	-0.25	V
		V _{IH} = 2.5 V, V _{IL} = 0 V (Note 12)	2.5	-0.6	
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note 12)	3.3	-0.8	
Quiet output minimum dynamic V _{OH}	V _{OHV}	V _{IH} = 1.8 V, V _{IL} = 0 V (Note 12)	1.8	1.5	V
		V _{IH} = 2.5 V, V _{IL} = 0 V (Note 12)	2.5	1.9	
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note 12)	3.3	2.2	

Note 12: Parameter guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Typ.	Unit
Input capacitance	C _{IN}	—	1.8, 2.5, 3.3	6	pF
Output capacitance	C _O	—	1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C _{PD}	f _{IN} = 10 MHz (Note 13)	1.8, 2.5, 3.3	60	pF

Note 13: CPD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC\ (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/20 \text{ (per bit)}$$

AC Test Circuit

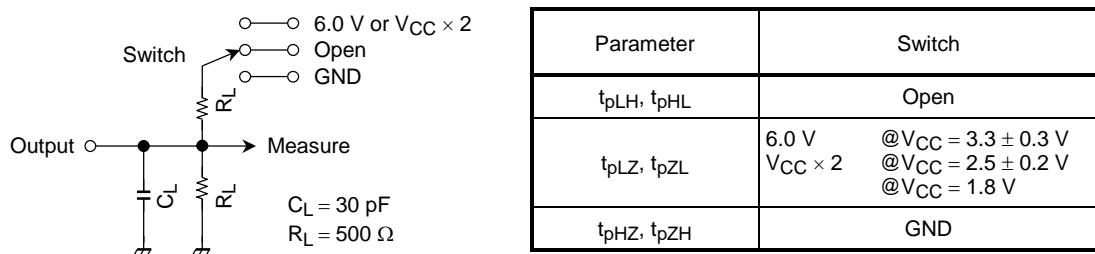
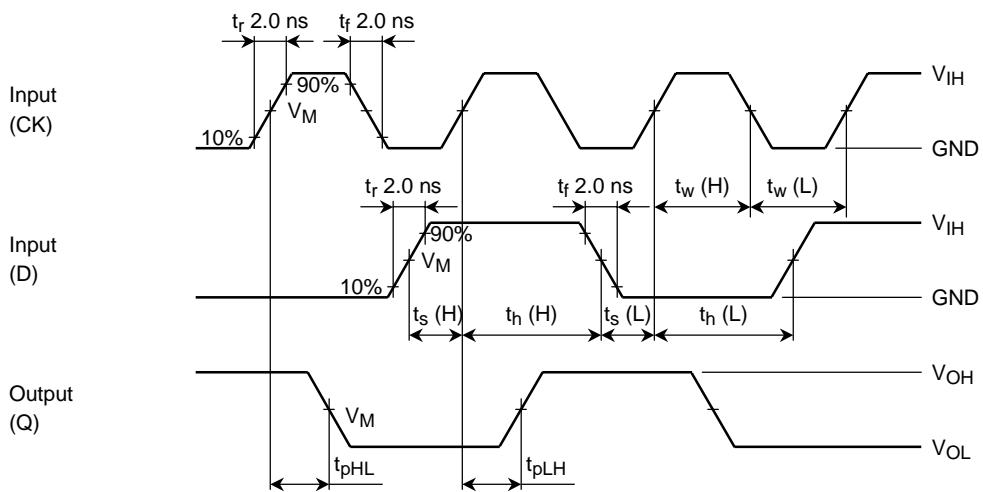


Figure 1

AC Waveform

Figure 2 $t_{pLH}, t_{pHL}, t_w, t_s, t_h$

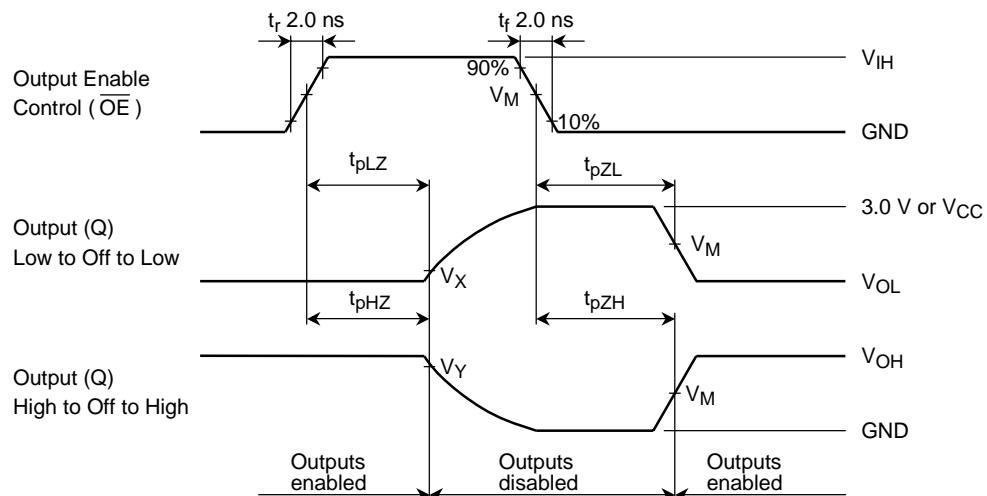


Figure 3 t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}

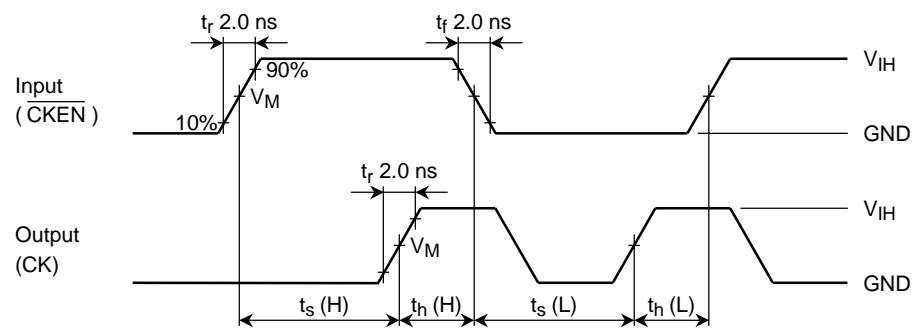


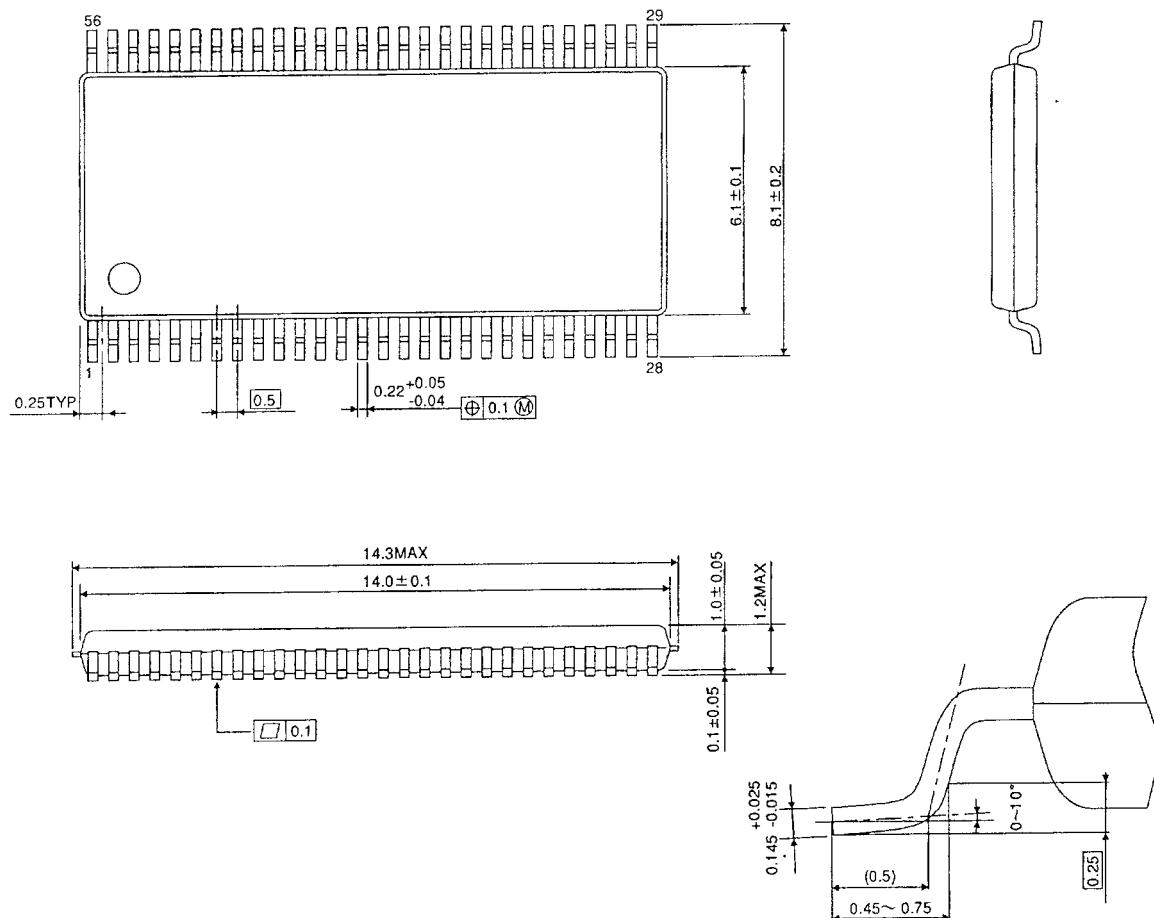
Figure 4 t_s , t_h

Symbol	V_{CC}		
	3.3 ± 0.3 V	2.5 ± 0.2 V	1.8 V
V_{IH}	2.7 V	V_{CC}	V_{CC}
V_M	1.5 V	$V_{CC}/2$	$V_{CC}/2$
V_X	$V_{OL} + 0.3$ V	$V_{OL} + 0.15$ V	$V_{OL} + 0.15$ V
V_Y	$V_{OH} - 0.3$ V	$V_{OH} - 0.15$ V	$V_{OH} - 0.15$ V

Package Dimensions

TSSOP56-P-0061-0.50

Unit : mm



Weight: 0.25 g (typ.)

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000707EBA

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